

**AMENDMENTS TO THE SPECIFICATION**

Please replace subtitle on page 1 with the following amended subtitle:

**TECHNICAL FIELD OF THE INVENTION**

Please replace paragraph 0001 with the following amended paragraph:

[0001] ~~The present invention relates to a~~ A method for manufacturing a semiconductor device is disclosed, ~~and, more specifically, to a method for manufacturing a semiconductor device~~ that is capable of securing the stability in a polishing process for forming a landing plug.

Please replace the title on page 2 with the following amended title:

**SUMMARY OF THE INVENTION DISCLOSURE**

Please replace paragraph 0004 with the following amended paragraph:

[0004] ~~The present invention is directed to a~~ A method for manufacturing a semiconductor device is disclosed that is capable of securing the stability of a polishing process for forming a landing plug, and the electric separation of word lines stably in a stable manner.

Please replace paragraph 0005 with the following amended paragraph:

[0005] According to ~~a preferred~~ an embodiment, ~~of the present invention,~~ ~~there is provided~~ a method for preventing ~~the~~ a short from ~~taking place by occurring~~ improving the ~~marginality of~~ marginal space when forming storage nodes or bit line self align contacts, wherein ~~the~~ a short otherwise could be generated between storage nodes or bit line self align contacts and word lines.

Please replace paragraph 0006 with the following amended paragraph:

[0006] ~~One aspect of the present invention is to provide a~~ One disclosed method ~~for manufacturing a semiconductor device comprising the steps of:~~ comprises preparing a semiconductor substrate defined as an active region and a field region; forming a number of word lines in the active region and the field region of the semiconductor substrate; depositing an insulator film over the upper part of a structure to insulate word lines;

patterning the insulator film to open word lines of the active region whereby forming a landing plug contact; depositing a poly silicon film to fill up the landing plug contact; performing a first polishing process using slurry including a first doping material and flattening the poly silicon film only, whereby exposing the insulator film; and forming a landing plug by performing a second polishing process using slurry including a second doping material and by flattening all the upper part of the structure.

Please replace paragraph 0007 with the following amended paragraph:

[0009] Figs. 1 to 7 are cross-sectional views showing a semiconductor device for explaining a disclosed method for manufacturing a semiconductor device ~~according to the present invention.~~

Please replace the title on page 4 with the following amended title:

DETAILED DESCRIPTION OF THE  
PRESENTLY PREFERRED EMBODIMENTS

Please replace paragraph 0010 with the following amended paragraph:

[0010] Now ~~the~~ certain preferred embodiments ~~according to the present invention~~ will be described with reference to the accompanying drawings. ~~Since preferred embodiments are provided for the purpose that the ordinary skilled in the art are able to understand the present invention, they may be modified in various manners and the scope of the present invention is not limited by the preferred embodiments described later.~~

Please replace paragraph 0019 with the following amended paragraph:

[0019] ~~According to the present invention, it~~ It is therefore possible to polish evenly and separate the adjacent word lines stably by performing the flattening process using slurry with a doping material added at the time of polishing process.

Please replace paragraph 0020 with the following amended paragraph:

[0020] Moreover, ~~according to the present invention,~~ it is possible to prevent ~~the~~ a short from ~~taking place~~ occurring by securing stably the polishing process for forming a landing plug stably and improving the ~~marginality of~~ marginal space when forming storage

nodes or bit line self align contacts, wherein the short otherwise could be generated between the storage nodes or bit line self align contacts and word lines.